

R-C Thermal Model Parameters

DESCRIPTION

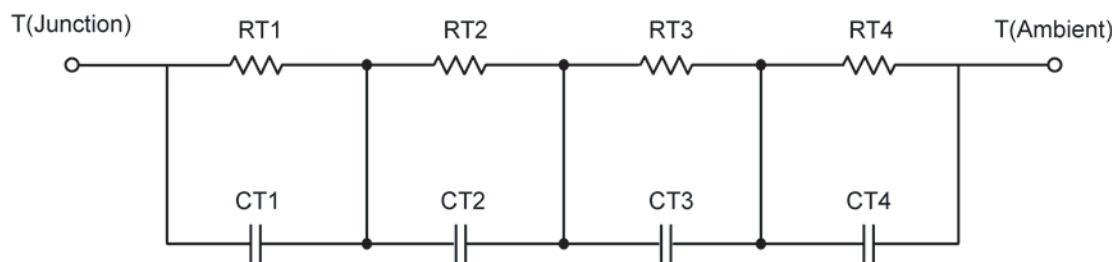
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-Spice, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-Spice Platform](#).

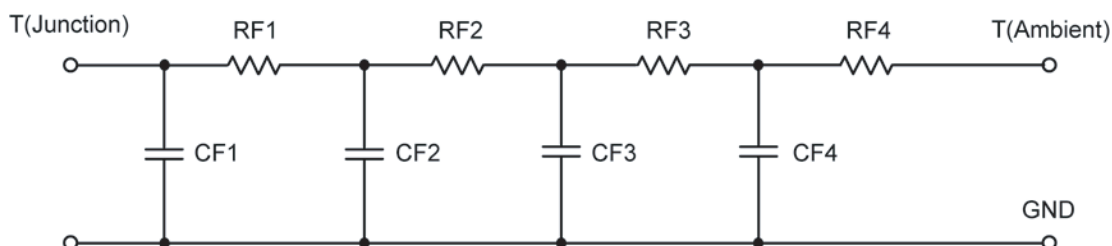
R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION

Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	1.6612	1.3034 m	N/A
RT2	12.9010	763.6878 m	N/A
RT3	9.6360	1.5671	N/A
RT4	45.6388	1.1817	N/A
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	1.7031 m	5.8945 m	N/A
CT2	400.0587 m	817.8719 μ	N/A
CT3	33.4493 m	13.5018 m	N/A
CT4	1.5835	11.1512 m	N/A

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION

R-C VALUES FOR FILTER CONFIGURATION			
Thermal Resistance ($^{\circ}\text{C}/\text{W}$)			
Junction to	Ambient	Case	Foot
RF1	8.8695	1.8143 m	N/A
RF2	5.2485	880.7106 m	N/A
RF3	12.5339	1.6900	N/A
RF4	43.0731	916.3063 m	N/A
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)			
Junction to	Ambient	Case	Foot
CF1	12.1549 m	172.7263 μ	N/A
CF2	167.0679 m	503.1365 μ	N/A
CF3	184.4786 μ	5.1743 m	N/A
CF4	1.3995	367.1440 μ	N/A

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

